

## Discrete POWER & Signal **Technologies**

## 1N/FDLL 914/A/B / 916/A/B / 4148 / 4448





THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL

#### **COLOR BAND MARKING** DEVICE 1ST BAND 2ND BAND FDLL914 BLACK BROWN FDLL914A FDLL914B BLACK BROWN GRAY BLACK FDLL916 FDLL916A BLACK BLACK RED WHITE BROWN BLACK BROWN FDLL916B FDLL4148 **BROWN**

FDLL4448

## **High Conductance Fast Diode**

Sourced from Process D3.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W <sub>IV</sub>	Working Inverse Voltage	75	V
Io	Average Rectified Current	200	mA
I <sub>F</sub>	DC Forward Current	300	mA
İf	Recurrent Peak Forward Current	400	mA
İf(surge)	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 4.0	A A
T <sub>stg</sub>	Storage Temperature Range	-65 to +200	°C
TJ	Operating Junction Temperature	175	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 200 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		1N/FDLL 914/A/B / 4148 / 4448	
P <sub>D</sub>	Total Device Dissipation	500	mW
	Derate above 25°C	3.33	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W

## **High Conductance Fast Diode**

(continued)

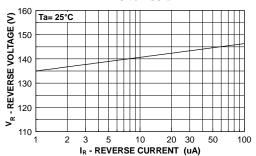
## **Electrical Characteristics**

TA = 25°C unless otherwise noted

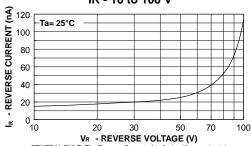
Symbol	Parameter	Test Conditions	Min	Max	Units
B <sub>V</sub>	Breakdown Voltage	I <sub>R</sub> = 100 μA	100		V
		$I_{R} = 5.0 \mu\text{A}$	75		V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 20 V		25	nA
		$V_R = 20 \text{ V}, T_A = 150^{\circ}\text{C}$		50	μΑ
		V <sub>R</sub> = 75 V		5.0	μA
V <sub>F</sub>	Forward Voltage 1N914B / 4448	I <sub>F</sub> = 5.0 mA	620	720	m۷
	1N916B	$I_F = 5.0 \text{ mA}$	630	730	mV
	1N914 / 916 / 4148	$I_F = 10 \text{ mA}$		1.0	V
	1N914A / 916A	$I_F = 20 \text{ mA}$		1.0	V
	1N916B	$I_F = 30 \text{ mA}$		1.0	V
	1N914B / 4448	$I_F = 100 \text{ mA}$		1.0	V
Co	Diode Capacitance				
	1N916/A/B / 4448	$V_R = 0$ , $f = 1.0 \text{ MHz}$		2.0	pF
	1N914/A/B / 4148	$V_R = 0$ , $f = 1.0 \text{ MHz}$		4.0	pF
T <sub>RR</sub>	Reverse Recovery Time	$I_F = 10 \text{ mA}, V_R = 6.0 \text{ V } (60 \text{ mA}),$		4.0	nS
		$I_{rr} = 1.0 \text{ mA}, R_L = 100 \Omega$			

## **Typical Characteristics**

## REVERSE VOLTAGE vs REVERSE CURRENT BV - 1.0 to 100 uA

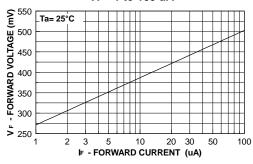


# REVERSE CURRENT vs REVERSE VOLTAGE IR - 10 to 100 V

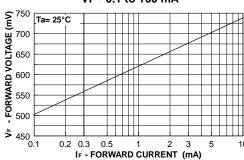


GENERAL RULE: The Reverse Current of a diode will approximate double for every ten (10) Degree C increase in Temperature

# FORWARD VOLTAGE vs FORWARD CURRENT VF - 1 to 100 uA



# FORWARD VOLTAGE vs FORWARD CURRENT VF - 0.1 to 100 mA

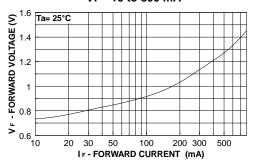


## **High Conductance Fast Diode**

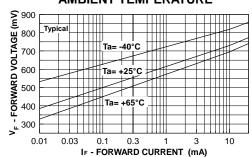
(continued)

## Typical Characteristics (continued)

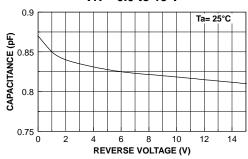
### FORWARD VOLTAGE vs FORWARD CURRENT VF - 10 to 800 mA



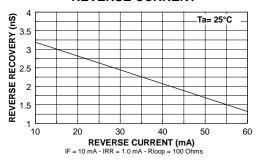
## VF - 0.01 - 20 mA (-40 to +65 Deg C) FORWARD VOLTAGE vs AMBIENT TEMPERATURE



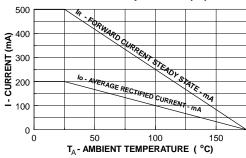
## CAPACITANCE vs REVERSE VOLTAGE VR = 0.0 to 15 V



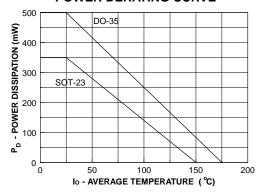
## REVERSE RECOVERY TIME vs REVERSE CURRENT



Average Rectified Current (Io) & Forward Current (I) versus Ambient Temperature (TA)



### **POWER DERATING CURVE**



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